## **Erratum**

Figures 12 through 17 were printed incorrectly in JOURNAL OF MATERIALS SCIENCE, volume 40, issue 13, July 2005, pages 3388–3390 in "Identification and characterization of diffusion barriers for Cu/SiC systems" by Glenn Sundberg, Pradeep Paul, Changmo Sung and Thomas Vasilos.

The correct versions are reprinted here:



*Figure 12* Cross-section of the  $\alpha$ -SiC rod after immersion in liquid Cu at 1150°C for 30 min. (a) SEM image showing the reaction zone of Cu and SiC (b) and (c) Energy dispersive X-ray maps of Cu and Si respectively.





*Figure 13* (a) TEM of Cu/SiC reaction zone showing the bright field image of the Cu-C and Cu-Si phases. (b) Electron diffraction pattern of the Cu-Si phase and (c) Electron diffraction of the Cu-C phase.



*Figure 14* SEM/EDS analysis of a cross-sectioned PVD TiN coated  $\alpha$ -SiC rod after immersion in liquid Cu at 1150°C for 30 min. (a) Secondary electron image (SEI) (b)–(d) X-ray maps.



*Figure 15* SEM/EDS analysis of a cross-sectioned CVD TiN/TiC/TiCN/TiN coated  $\alpha$ -SiC rod after immersion in liquid Cu at 1150°C for 30 min. (a) Secondary electron image (SEI) (b)–(d) X-ray maps.



*Figure 16* SEM/EDS analysis of a cross-sectioned CVD TiN/TiC/Al<sub>2</sub>O<sub>3</sub> coated  $\alpha$ -SiC rod after immersion in liquid Cu at 1150°C for 30 min. (a) Secondary electron image (SEI) (b)–(e) X-ray maps.



*Figure 17* SEM/EDS analysis of a cross-sectioned CVD Diamond Like Carbon (DLC) coated  $\alpha$ -SiC rod after immersion in liquid Cu at 1150°C for 30 min. (a) Secondary electron image (SEI) (b)–(c) X-ray maps.